

## AM27LS03

### *64-Bit Low-Power Inverting-Output Bipolar RAM*

The AM27LS03 is a 64-bit RAM built using Schottky diode clamped transistors in conjunction with internal ECL circuitry and are ideal for use in scratch pad and high-speed buffer memory applications. Each memory is organized as a fully decoded 16-word memory of 4 bits per word. Easy memory expansion is provided by an active LOW chip select (CS) input and three-state outputs (AM27LS03).

An active LOW Write line (WE) controls the writing/reading operation of the memory. When the chip select and write lines are LOW the information on the four data inputs D0 to D3 is written into the addressed memory word and preconditions the output circuitry so that correct data is present at the outputs when the write cycle is complete. This preconditioning operation insures minimum write recovery times by eliminating the “write recovery glitch.”

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### **Rochester Electronics Manufactured Components**

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All recreations are done with the approval of the OCM.

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceeds the OCM data sheet.

### **Quality Overview**

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-38535
  - Class Q Military
  - Class V Space Level
- Qualified Suppliers List of Distributors (QSLD)
  - Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

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*The original manufacturer’s datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OEM specifications. ‘Typical’ values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.*

# Am27LS03

64-Bit Low-Power Inverting-Output Bipolar RAM



Am27LS03

Advanced Micro Devices

## DISTINCTIVE CHARACTERISTICS

- Fully decoded 16 word x 4-bit low-power Schottky RAMs
- Low Power
- Internal ECL circuitry for optimum speed/power performance over voltage and temperature
- Output preconditioned during write to eliminate write recovery glitch
- Available with three-state outputs (Am27LS03)
- Pin-compatible replacements for 74LS189, (use Am27LS03)

## GENERAL DESCRIPTION

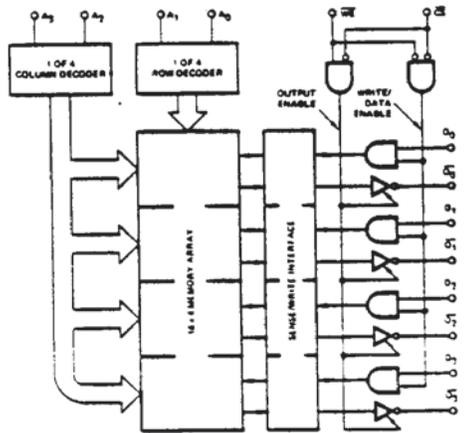
The Am27LS03 is a 64-bit RAM built using Schottky diode clamped transistors in conjunction with internal ECL circuitry and are ideal for use in scratch pad and high-speed buffer memory applications. Each memory is organized as a fully decoded 16-word memory of 4 bits per word. Easy memory expansion is provided by an active LOW chip select (CS) input and three-state outputs (Am27LS03).

An active LOW Write line ( $\overline{WE}$ ) controls the writing/reading operation of the memory. When the chip select and write lines are LOW the information on the four data inputs  $D_0$  to  $D_3$  is written into the addressed memory word and preconditioned the output circuitry so that correct data is present at the outputs when the write cycle is complete. This preconditioning operation insures minimum write recovery times by eliminating the "write recovery glitch."

Reading is performed with the chip select line LOW and the write line HIGH. The information stored in the addressed word is read out on the four inverting outputs  $\overline{O}_0$  to  $\overline{O}_3$ .

During the writing operation or when the chip select line is HIGH the four outputs of the memory go to an inactive high-impedance state.

## BLOCK DIAGRAM



8D000551

## MODE SELECT TABLE

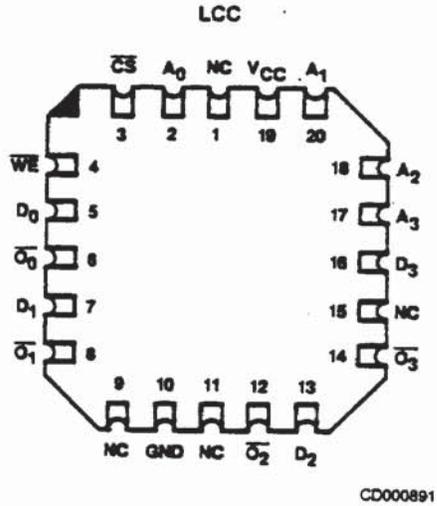
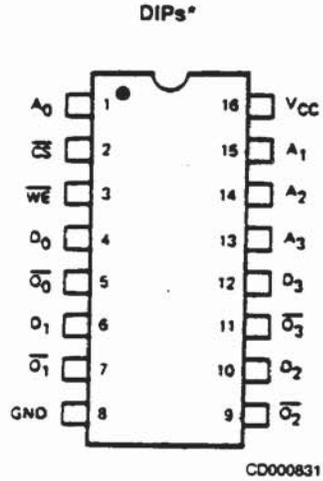
Input		Data Output Status $\overline{O}_0 - \overline{O}_3$	Mode
CS	WE		
L	L	Output Disabled	Write
L	H	Selected Word (Inverted)	Read
H	X	Output Disabled	Deselect

H = HIGH  
L = LOW  
X = Don't Care

## PRODUCT SELECTOR GUIDE

Access Time	55 ns	65 ns
$I_{CC}$	35 mA	38 mA
Temperature Range	C	M
Three-State	Am27LS03	

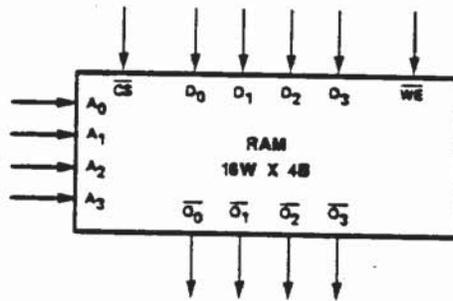
**CONNECTION DIAGRAMS**  
Top View



\*Also available in 16-Pin Carpack. Connections identical to DIPs.

Note: Pin 1 is marked for orientation.

**LOGIC SYMBOL**



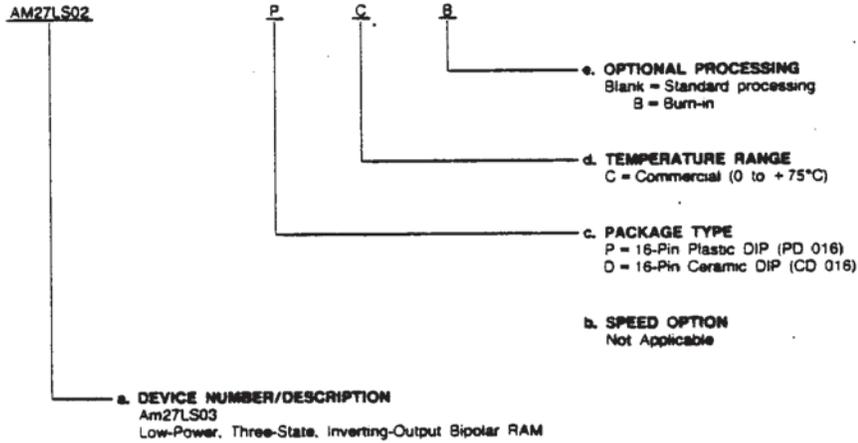
LS000212

## ORDERING INFORMATION

### Standard Products

AMD standard products are available in several packages and operating ranges. The order number (Valid Combination) is formed by a combination of:

- a. Device Number
- b. Speed Option (if applicable)
- c. Package Type
- d. Temperature Range
- e. Optional Processing



Valid Combinations	
AM27LS03	PC, PCB, DC, DCB

### Valid Combinations

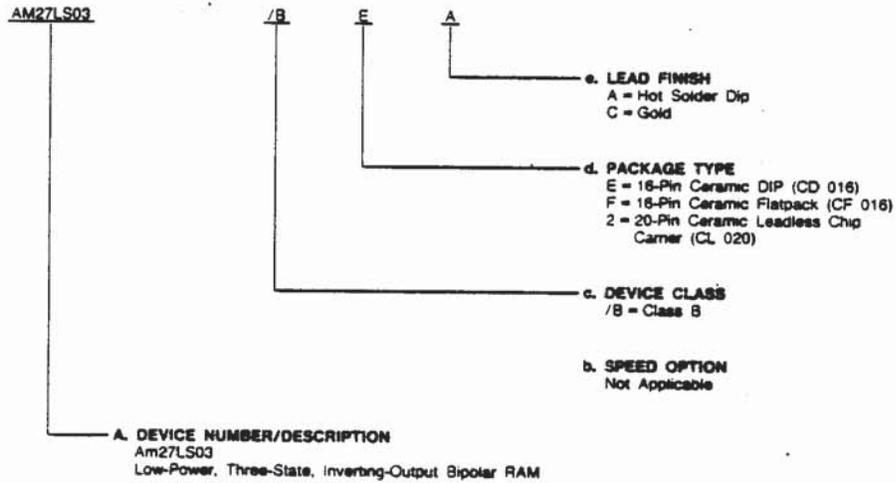
Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations, to check on newly released valid combinations, and to obtain additional data on AMD's standard military grade products.

**ORDERING INFORMATION (Cont'd.)**

APL Products

AMD products for Aerospace and Defense applications are available in several packages and operating ranges. APL (Approved Products List) products are fully compliant with MIL-STD-883C requirements. The order number (Valid Combination) for APL products is formed by a combination of:

- a. Device Number
- b. Speed Option (if applicable)
- c. Device Class
- d. Package Type
- e. Lead Finish



Valid Combinations	
AM27LS03	/BEA, /BFA, /B2C

**Valid Combinations**

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations or to check for newly released valid combinations.

**Group A Tests**

Group A tests consist of Subgroups  
1, 2, 3, 9, 10, 11.

**ABSOLUTE MAXIMUM RATINGS**

Storage Temperature ..... -65 to +150°C  
 Ambient Temperature with  
 Power Applied ..... -55 to +125°C  
 Supply Voltage ..... -0.5 V to +7.0 V  
 DC Voltage Applied to Outputs ..... -0.5 V to +V<sub>CC</sub> Max.  
 DC Input Voltage ..... -0.5 V to +5.5 V  
 Output Current into Outputs ..... 20 mA  
 DC Input Current ..... -30 mA to +5 mA

*Stresses above those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent device failure. Functionality at or above these limits is not implied. Exposure to absolute maximum ratings for extended periods may affect device reliability.*

**OPERATING RANGES**

Commercial (C) Devices  
 Temperature ..... 0 to +75°C  
 Supply Voltage ..... +4.75 V to +5.25 V  
 Military\* (M) Devices  
 Temperature ..... -55 to +125°C  
 Supply Voltage ..... +4.5 V to +5.5 V

*Operating ranges define those limits between which the functionality of the device is guaranteed.*

(See Note 4)

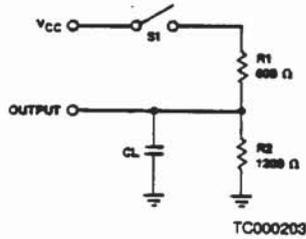
\*Military product 100% tested at T<sub>C</sub> = +25°C, +125°C, and -55°C.

**DC CHARACTERISTICS** over operating ranges unless otherwise specified (for APL products, Group A, Subgroups 1, 2, 3 are tested unless otherwise noted)

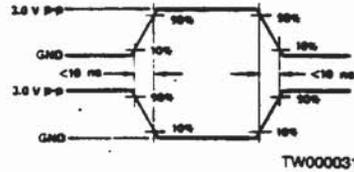
Parameter Symbol	Parameter Description	Test Conditions	Am27LS02/27LS03			Unit
			Min.	Typ.	Max.	
V <sub>OH</sub>	Output HIGH Voltage	V <sub>CC</sub> = Min., V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OH</sub> = -5.2 mA COM'L I <sub>OH</sub> = -2.0 mA MIL	2.4	3.0		V
V <sub>OL</sub>	Output LOW Voltage	V <sub>CC</sub> = Min., V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OL</sub> = 8 mA I <sub>OL</sub> = 10 mA		320 350	450 500	mV
V <sub>IH</sub>	Input HIGH Level	Guaranteed Input Logical HIGH Voltage for All Inputs (Note 2)	2.0			V
V <sub>IL</sub>	Input LOW Level	Guaranteed Input Logical LOW Voltage for All Inputs (Note 2)			0.8	V
I <sub>IL</sub>	Input LOW Current	V <sub>CC</sub> = Max., V <sub>IN</sub> = 0.40 V WE, D <sub>0</sub> -D <sub>3</sub> , A <sub>0</sub> -A <sub>3</sub> CS		-15 -30	-250 -250	μA
I <sub>IH</sub>	Input HIGH Current	V <sub>CC</sub> = Max., V <sub>IN</sub> = 2.7 V		0	10	μA
I <sub>SC</sub> (Note 3)	Output Short Circuit Current	V <sub>CC</sub> = Max., V <sub>OUT</sub> = 0.0 V	-20	-45	-90	mA
I <sub>CC</sub>	Power Supply Current	All Inputs = GND Outputs = Open V <sub>CC</sub> = Max.		27	35 38	mA
V <sub>CL</sub>	Input Clamp Voltage	V <sub>CC</sub> = Min., I <sub>IN</sub> = -18 mA		-0.875	-1.2	V
I <sub>CEX</sub>	Output Leakage Current	V <sub>CS</sub> = V <sub>IH</sub> or V <sub>WE</sub> = V <sub>IL</sub> V <sub>OUT</sub> = 2.4 V, V <sub>CC</sub> = Max. V <sub>CS</sub> = V <sub>IH</sub> or V <sub>WE</sub> = V <sub>IL</sub> V <sub>OUT</sub> = 0.4 V, V <sub>CC</sub> = Max.		0	40	μA
		(Note 2)	-40	0		μA

- Notes: 1. Typical limits are at V<sub>CC</sub> = 5.0 V and T<sub>A</sub> = 25°C.  
 2. These are absolute voltages with respect to device ground pin and include all overshoots due to system and/or tester noise. Do not attempt to test these values without suitable equipment.  
 3. Not more than one output should be shorted at a time. Duration of the short circuit should not be more than one second.  
 4. Operating specifications with adequate time for temperature stabilization and transverse air flow exceeding 100 linear feet per minute. Conformance testing performed instantaneously where T<sub>A</sub> = T<sub>C</sub> = T<sub>J</sub>.  
 θ<sub>JA</sub> ≈ 50°C/w (with moving air) for ceramic DIPs.  
 θ<sub>JC</sub> ≈ 10 - 17°C/w for flatpack and leadless chip carrier.

**SWITCHING TEST  
CIRCUIT**



**SWITCHING TEST  
WAVEFORM**



**KEY TO SWITCHING  
WAVEFORMS**

WAVEFORM	INPUTS	OUTPUTS
	MUST BE STEADY	WILL BE STEADY
	MAY CHANGE FROM H TO L	WILL BE CHANGING FROM H TO L
	MAY CHANGE FROM L TO H	WILL BE CHANGING FROM L TO H
	DON'T CARE; ANY CHANGE PERMITTED	CHANGING; STATE UNKNOWN
	DOES NOT APPLY	CENTER LINE IS HIGH IMPEDANCE "OFF" STATE

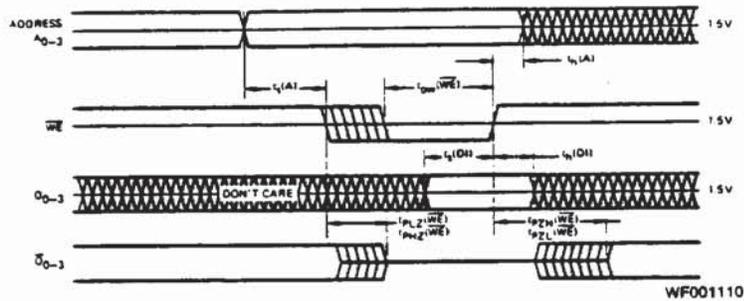
KS000010

**SWITCHING CHARACTERISTICS** over operating range unless otherwise specified (for APL products, Group A, Subgroups 9, 10, 11 are tested unless otherwise noted)

No.	Parameter Symbol	Parameter Description	Am27LS03				Unit
			C Devices		M Devices		
			Min.	Max.	Min.	Max.	
1	$t_{PLH}(A)$	Delay from Address to Output		55		65	ns
2	$t_{PHL}(A)$						
3	$t_{PZH}(CS)$	Delay from Chip Select (LOW) to Active Output and Correct Data		30		35	ns
4	$t_{PZL}(CS)$						
5	$t_{PZH}(WE)$	Delay from Write Enable (HIGH) to Active Output and Correct Data (Write Recovery-See Note 1)		30		35	ns
6	$t_{PZL}(WE)$						
7	$t_S(A)$	Setup Time Address (Prior to Inversion of Write)	0		0		ns
8	$t_H(A)$	Hold Time Address (After Termination of Write)	0		0		ns
9	$t_S(DI)$	Setup Time Data Input (Prior to Termination of Write)	45		55		ns
10	$t_H(DI)$	Hold Time Data Input (After Termination of Write)	0		0		ns
11	$t_{pw}(WE)$	Min Write Enable Pulse Width to Insure Write	45		55		ns
12	$t_{PHZ}(CS)$	Delay from Chip Select (HIGH) to Inactive Output (HI-Z)		30		35	ns
13	$t_{PLZ}(CS)$						
14	$t_{PLZ}(WE)$	Delay from Write Enable (LOW) to Inactive Output (HI-Z)		30		35	ns
15	$t_{PHZ}(WE)$						

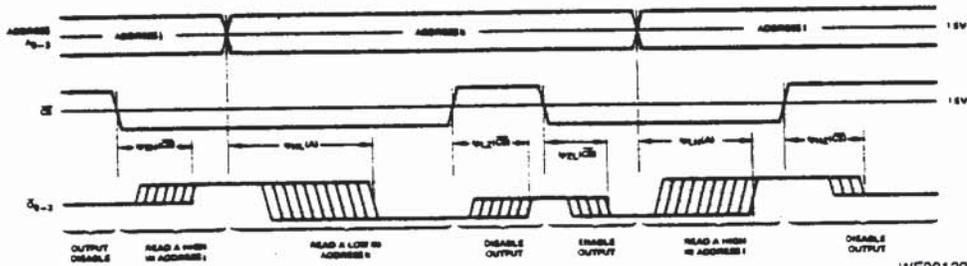
- Notes: 1. Output is preconditioned to data in during write to insure correct data is present on all outputs when write is terminated. (No write recovery glitch.)  
 2.  $t_{PLH}(A)$  and  $t_{PHL}(A)$  are tested with  $S_1$  closed and  $C_L = 30\text{ pF}$  with both input and output timing referenced to 1.5 V.  
 3. For 3-state output,  $t_{PZH}(WE)$  and  $t_{PZH}(CS)$  are measured with  $S_1$  open,  $C_L = 50\text{ pF}$  and with both the input and output timing referenced to 1.5 V.  $t_{PZL}(WE)$  and  $t_{PZL}(CS)$  are measured with  $S_1$  closed,  $C_L = 50\text{ pF}$  and with both the input and output timing referenced to 1.5 V.  $t_{PHZ}(WE)$  and  $t_{PHZ}(CS)$  are measured with  $S_1$  open and  $C_L \leq 5\text{ pF}$  and are measured between the 1.5 V level on the input to the  $V_{OH} - 500\text{ mV}$  level on the output.  $t_{PLZ}(WE)$  and  $t_{PLZ}(CS)$  are measured with  $S_1$  closed and  $C_L \leq 5\text{ pF}$  and are measured between the 1.5 V level on the input and the  $V_{OL} + 500\text{ mV}$  level on the output.

### SWITCHING WAVEFORMS



#### Write Mode

**Write Cycle Timing.** The cycle is initiated by an address change. After  $t_1(A)$  min, the write enable may begin. The chip select must also be LOW for writing. Following the write pulse,  $t_1(OH)$  min must be allowed before the address may be changed again. The output will be inactive (floating for the Am27LS03) while the write enable is (WE) LOW.



#### Read Mode

Switching delays from address and chip select inputs to the data output. For the Am27LS03 disabled output is "OFF", represented by a single center line. For the Am27LS02, a disabled output is HIGH.